



N-Channel Depletion-Mode Vertical DMOS FET

Features

- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakages

Applications

- ▶ Normally-on switches
- ▶ Battery operated systems
- ▶ Converters
- ▶ Linear amplifiers
- ▶ Constant current sources
- ▶ Telecom

General Description

The Supertex DN1509 is suitable for high voltage transient protection for LDO in automobile applications during “load dump” conditions.

This low threshold, depletion-mode (normally-on) transistor utilizes an advanced vertical DMOS structure and Supertex’s well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex’s vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV _{DSX} /BV _{DGX} (V)	R _{DS(ON)} (max) (Ω)	I _{DSS} (typ) (mA)
	TO-243AA (SOT-89)			
DN1509	DN1509N8-G	90	6.0	540

-G indicates package is RoHS compliant ('Green')



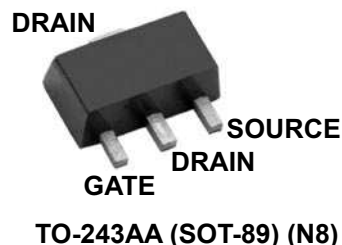
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSX}
Drain-to-gate voltage	BV _{DGX}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6mm from case for 10 seconds.

Pin Configuration



Product Marking

DN5AW W = Code for week sealed
 _____ = “Green” Packaging
TO-243AA (SOT-89) (N8)

Thermal Characteristics

Package	I _D (continuous) [†] (mA)	ID (pulsed) (mA)	Power Dissipation @T _A = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	I _{DR} [‡] (mA)	I _{DRM} (mA)
TO-243AA	360	500	1.6 [‡]	15	78 [‡]	360	500

Notes:

- [†] I_D (continuous) is limited by max rated T_j of 150°C.
- [‡] Mounted on FR4 board, 25mm x 25mm x 1.57mm.

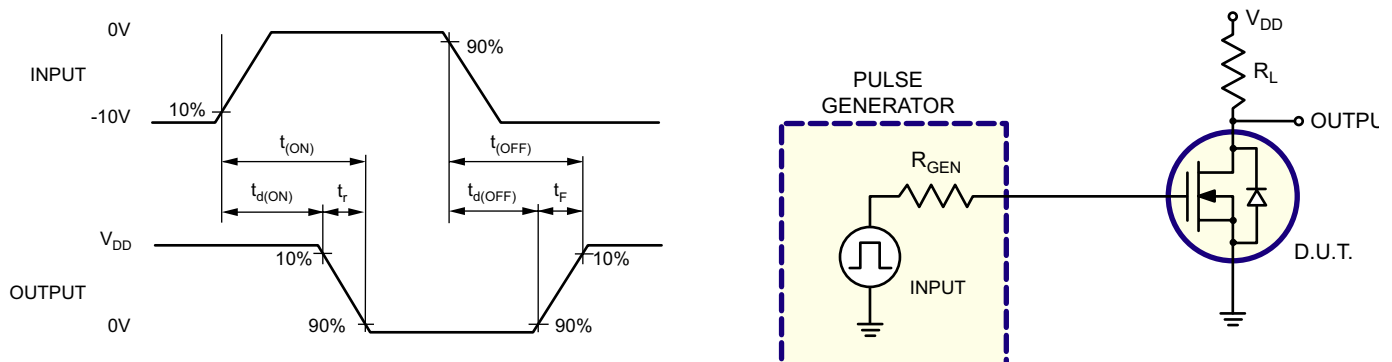
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV _{DSX}	Drain-to-source breakdown voltage	90	-	-	V	V _{GS} = -5V, I _D = 1.0μA
V _{GS(OFF)}	Gate-to-source off voltage	-1.8	-	-3.5	V	I _D = 10μA
ΔV _{GS(OFF)}	V _{GS(OFF)} change with temperature	-	-	-4.5	mV/°C	V _{DS} = 15V, I _D = 10μA
I _{GSS}	Gate body leakage	-	-	100	nA	V _{GS} = ±20V, V _{DS} = 0V
I _{D(OFF)}	Drain-to-source leakage current	-	-	1.0	μA	V _{DS} = Max rating, V _{GS} = -5.0V
		-	-	1.0	mA	V _{DS} = 0.8 Max Rating, V _{GS} = -5.0V, T _A = 125°C
I _{DSS}	Saturated drain-to-source current	300	540	-	mA	V _{GS} = 0V, V _{DS} = 25V
R _{DS(ON)}	Static Drain-to-source on-state resistance	-	3.2	6.0	Ω	V _{GS} = 0V, I _D = 200mA
ΔR _{DS(ON)}	Change in R _{DS(ON)} with temperature	-	-	1.1	%/°C	V _{GS} = 0V, I _D = 200mA
G _{FS}	Forward transconductance	200	-	-	mmho	V _{DS} = 10V, I _D = 200mA
C _{ISS}	Input capacitance	-	70	150	pF	V _{GS} = -10V, V _{DS} = 25V, f = 1MHz
C _{OSS}	Common source output capacitance	-	20	40		
C _{RSS}	Reverse transfer capacitance	-	6.0	15		
t _{d(ON)}	Turn-on delay time	-	12	30	ns	V _{DD} = 25V, I _D = 100mA, R _{GEN} = 25Ω
t _r	Rise time	-	16	45		
t _{d(OFF)}	Turn-off delay time	-	15	45		
t _f	Fall time	-	25	60		
V _{SD}	Diode forward voltage drop	-	-	1.8	V	V _{GS} = 0V, I _{SD} = 500mA
t _{rr}	Reverse recovery time	-	400	-	ns	V _{GS} = 0V, I _{SD} = 500mA

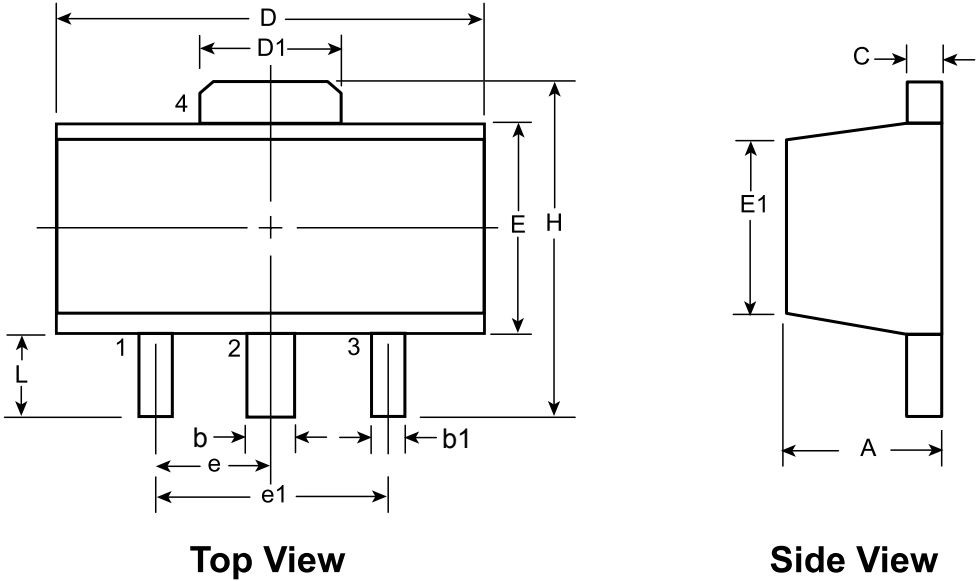
Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit



3-Lead TO-243AA (SOT-89) Package Outline (N8)



Top View

Side View

Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.13	1.50 BSC	3.00 BSC	3.94	0.89
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version D070908.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

Supertex inc. does not recommend the use of its products in life support applications, and will not knowingly sell them for use in such applications unless it receives an adequate "product liability indemnification insurance agreement." Supertex inc. does not assume responsibility for use of devices described, and limits its liability to the replacement of the devices determined defective due to workmanship. No responsibility is assumed for possible omissions and inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications refer to the Supertex inc. website: <http://www.supertex.com>.